

A METHOD OF DEPOSITING TUNGSTEN NITRIDE
USING A SOURCE GAS COMPRISING SILICON

ABSTRACT

A method for depositing tungsten nitride uses a source gas mixture having a silicon based gas for depositing the tungsten nitride to overlie a deposition substrate. A non-planar storage capacitor has a tungsten nitride capacitor electrode.

"Express Mail" mailing label number: EV041119781US
Date of Deposit: December 5, 2001

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